BC307B, BC307C

Amplifier Transistors

PNP Silicon

Features

• Pb–Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V _{CEO}	-45	Vdc
Collector – Base Voltage	V _{CBO}	-50	Vdc
Emitter – Base Voltage	V _{EBO}	-5.0	Vdc
Collector Current – Continuous	۱ _C	-100	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	350 2.8	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	1.0 8.0	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

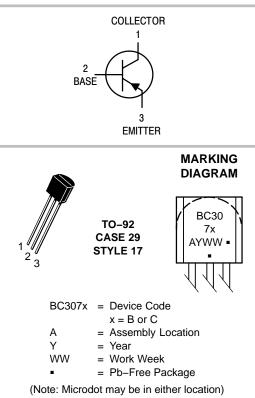
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	R_{\thetaJA}	357	°C/W
Thermal Resistance, Junction-to-Case	$R_{ extsf{ heta}JC}$	125	°C/W



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ORDERING INFORMATION

Device	Package	Shipping [†]			
BC307B	TO-92	5000 Units / Box			
BC307BG	TO–92 (Pb–Free)	5000 Units / Box			
BC307BRL1	TO-92	2000 / Tape & Reel			
BC307BRL1G	TO–92 (Pb–Free)	2000 / Tape & Reel			
BC307BZL1	TO-92	2000 / Ammo Box			
BC307BZL1G	TO–92 (Pb–Free)	2000 / Ammo Box			
BC307C	TO-92	5000 Units / Box			
BC307CG	TO–92 (Pb–Free)	5000 Units / Box			

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

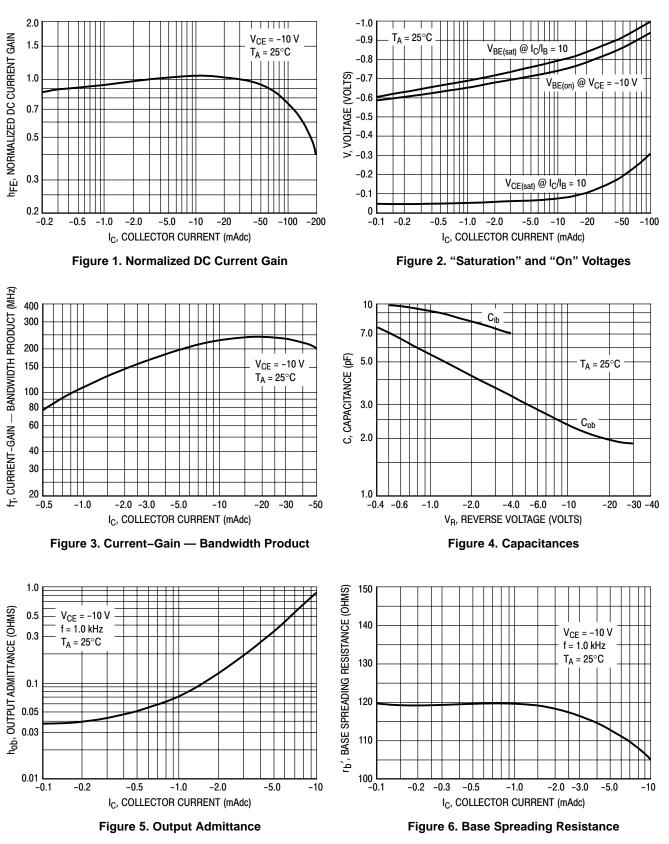
BC307B, BC307C

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS						
Collector – Emitter Breakdown Voltage $(I_C = -2.0 \text{ mAdc}, I_B = 0)$		V _{(BR)CEO}	-45	_	_	Vdc
Emitter – Base Breakdown Voltage $(I_E = -100 \ \mu Adc, I_C = 0)$		V _{(BR)EBO}	-5.0	_	_	Vdc
Collector–Emitter Leakage Current ($V_{CES} = -50 \text{ V}, V_{BE} = 0$) ($V_{CES} = -50 \text{ V}, V_{BE} = 0$) T _A = 125°C		I _{CES}	-	-0.2 -0.2	-15 -4.0	nAdc μA
ON CHARACTERISTICS						
DC Current Gain (I _C = -10μ Adc, V _{CE} = -5.0 Vdc)	BC307B BC307C	h _{FE}		150 270		-
$(I_{C} = -2.0 \text{ mAdc}, V_{CE} = -5.0 \text{ Vdc})$	BC307 BC307B BC307C		120 200 420	_ 290 500	800 460 800	
$(I_{C} = -100 \text{ mAdc}, V_{CE} = -5.0 \text{ Vdc})$	BC307B BC307C			180 300		
$ Collector - Emitter Saturation Voltage \\ (I_C = -10 mAdc, I_B = -0.5 mAdc) \\ (I_C = -10 mAdc, I_B = see Note 1) \\ (I_C = -100 mAdc, I_B = -5.0 mAdc) $		V _{CE(sat)}	- - -	-0.10 -0.30 -0.25	-0.3 -0.6 -	Vdc
Base – Emitter Saturation Voltage ($I_C = -10 \text{ mAdc}, I_B = -0.5 \text{ mAdc}$) ($I_C = -100 \text{ mAdc}, I_B = -5.0 \text{ mAdc}$)		V _{BE(sat)}	-	-0.7 -1.0		Vdc
Base–Emitter On Voltage ($I_C = -2.0 \text{ mAdc}, V_{CE} = -5.0 \text{ Vdc}$)		V _{BE(on)}	-0.55	-0.62	-0.7	Vdc
DYNAMIC CHARACTERISTICS				•	L	
Current–Gain – Bandwidth Product ($I_C = -10$ mAdc, $V_{CE} = -5.0$ Vdc, f = 100 MHz)		f _T	_	280	_	MHz
Common Base Capacitance $(V_{CB} = -10 \text{ Vdc}, I_C = 0, f = 1.0 \text{ MHz})$		C _{cbo}	-	-	6.0	pF
Noise Figure (I _C = -0.2 mAdc, V _{CE} = -5.0 Vdc, R _S = 2.0 kΩ, f = 1.0 kHz)		NF	_	2.0	10	dB

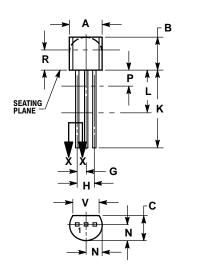
BC307B, BC307C

TYPICAL CHARACTERISTICS



PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 **ISSUE AL**





NOTES

DIMENSIONING AND TOLERANCING PER ANSI 1.

Y14.5M, 1982. CONTROLLING DIMENSION: INCH.

3.

CONTIGUEING DIMENSION. INC. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM. 4.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.175	0.205	4.45	5.20	
В	0.170	0.210	4.32	5.33	
С	0.125	0.165	3.18	4.19	
D	0.016	0.021	0.407	0.533	
G	0.045	0.055	1.15	1.39	
Н	0.095	0.105	2.42	2.66	
J	0.015	0.020	0.39	0.50	
K	0.500		12.70		
L	0.250		6.35		
Ν	0.080	0.105	2.04	2.66	
Ρ		0.100		2.54	
R	0.115		2.93		
V	0.135		3.43		

STYLE 17: PIN 1. COLLECTOR

BASE 2. 3. EMITTER

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